Session HH

Device Modeling and CAD

Chairman:

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This session focuses on the treatment of active devices in CAD of microwave circuits and systems. Active device modeling and analysis has seen tremendous progress over the last several years. Recent developments include meaningful temperature dependent physical models of FET devices, derived from numerical solutions to semiconductor equations and process parameters. Interest and use of time domain analysis has also been increasing steadily, and breakthroughs are evident in a very general treatment of frequency domain data in time domain simulations. An important future objective for this area will be to arm designers with the CAD tools needed to include the unavoidable electrical and thermal effects of the final packaged environment in time and frequency domain simulations.

8:30 a.m.–10:00 a.m., Thursday, June 17, 1993
Room 218/219